PB51 • PB51A

Power Booster Amplifier

FEATURES

- Wide Supply Range – ±15V to ±150V
- High Output Current –
    1.5A Continuous (PB51),
    2.0A Continuous (PB51A)
- Voltage and Current Gain
- High Slew –
    50V/µs Minimum (PB51)
    75V/µs Minimum (PB51A)
- Programmable Output Current Limit
- High Power Bandwidth – 320 kHz Minimum
- Low Quiescent Current – 12mA Typical
- Evaluation Kit – EK29

APPLICATIONS

- High Voltage Instrumentation
- Electrostatic Transducers & Deflection
- Programmable Power Supplies up to 280V P-P

DESCRIPTION

The PB51 is a high voltage, high current amplifier designed to provide voltage and current gain for a small signal, general purpose op amp. Including the power booster within the feedback loop of the driver amplifier results in a composite amplifier with the accuracy of the driver and the extended output voltage range and current capability of the booster. The PB51 can also be used without a driver in some applications, requiring only an external current limit resistor to function properly.

The output stage utilizes complementary MOSFETs, providing symmetrical output impedance and eliminating second breakdown limitations imposed by Bipolar Transistors. Internal feedback and gainset resistors are provided for a pin-strapable gain of 3. Additional gain can be achieved with a single external resistor. Compensation is not required for most driver/gain configurations, but can be accomplished with a single external capacitor. Enormous flexibility is provided through the choice of driver amplifier, current limit, supply voltage, voltage gain, and compensation.

This hybrid circuit utilizes a beryllia (BeO) substrate, thick film resistors, ceramic capacitors and semiconductor chips to maximize reliability, minimize size and give top performance.

Ultrasonically bonded aluminum wires provide reliable interconnections at all operating temperatures. The 12-pin Power SIP is electrically isolated.
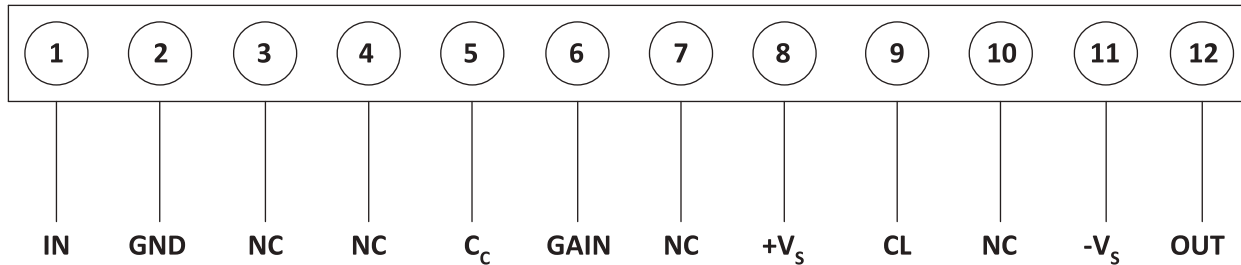
TYPICAL CONNECTION

Figure 1: Typical Connection
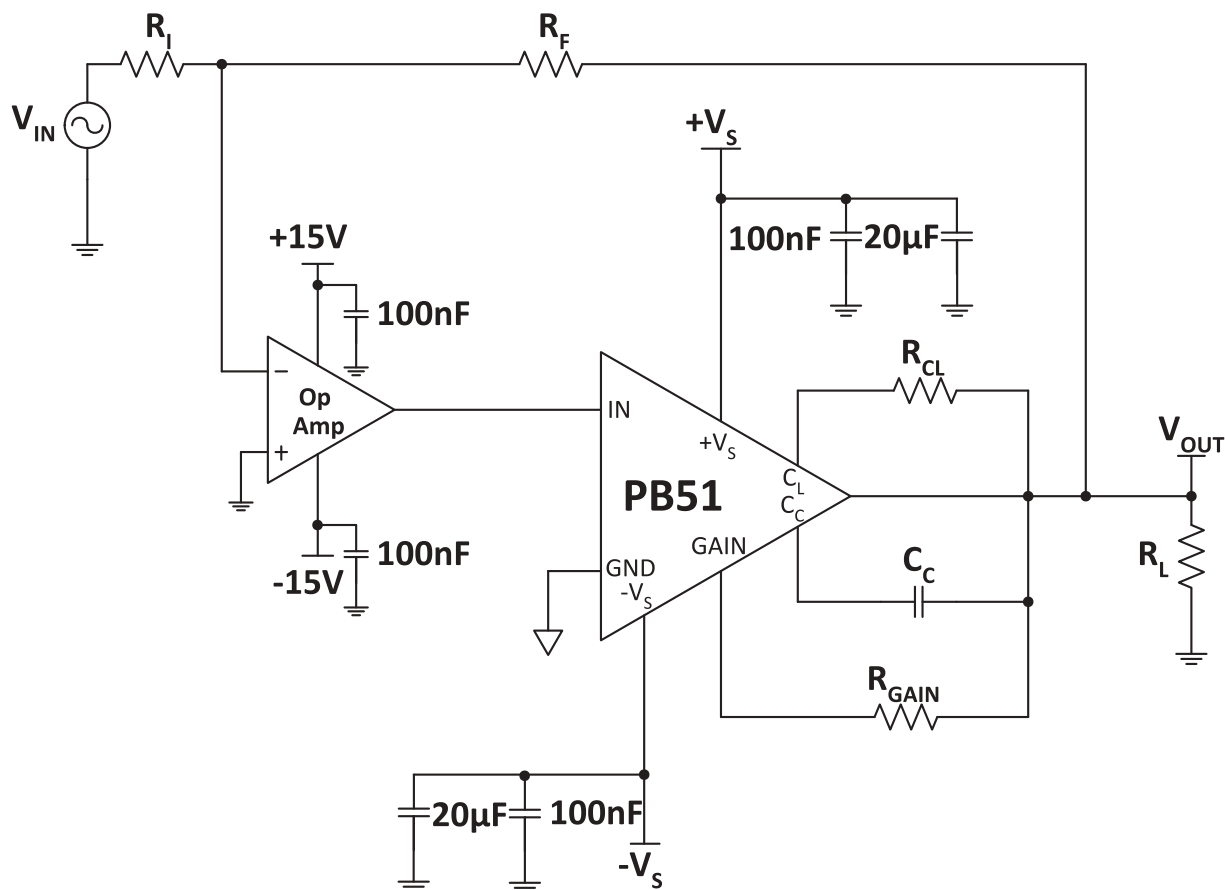
PINOUT AND DESCRIPTION TABLE

Figure 2: External Connections

1	2	3	4	5	6	7	8	9	10	11	12
IN	GND	NC	NC	C_C	GAIN	NC	$+V_S$	CL	NC	$-V_S$	OUT

Pin Number	Name	Description
1	IN	The output. Connect this pin to load and to the feedback resistors.
2	GND	Ground. Connect to same ground as referenced by input amplifier.
5	CC	Compensation capacitor connection. Select value based on Phase Compensation. See applicable section.
6	GAIN	Gain resistor pin. Connect R_{GAIN} between GAIN and OUT. This will specify the gain for the power booster itself, not the composite amplifier. See applicable section.
8	+Vs	The positive supply rail.
9	CL	Connect to the current limit resistor. Output current flows into/out of these pins through R_{CL}. The output pin and the load are connected to the other side of R_{CL}.
11	-Vs	The negative supply rail.
12	OUT	The output. Connect this pin to load and to the feedback resistors.
3, 4, 7, 10	NC	No connection.

SPECIFICATIONS

The power supply voltage specified under typical (TYP) applies, T_C = 25°C unless otherwise noted.

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Min	Max	Units
Supply Voltage, total	+V_S to -V_S		300	V
Output Current, within SOA	I_O		2	A
Power Dissipation, internal @ T_C = 25°C[1]	P_D		83	W
Input Voltage, referred to COM	V_{IN}	-15	15	V
Temperature, pin solder, 10s max.			260	°C
Temperature, junction [1]	T_J		175	°C
Temperature Range, storage		-55	+125	°C
Operating Temperature Range, case	T_C	-40	+85	°C

1. Long term operation at the maximum junction temperature will result in reduced product life. Derate internal power dissipation to achieve high MTTF (Mean Time to Failure).

CAUTION The PB51A is constructed from MOSFET devices. ESD handling procedures must be observed. The substrate contains beryllia (BeO). Do not crush, machine or subject to temperatures in excess of 850°C to avoid generating toxic fumes.

INPUT

Parameter	Test Conditions	PB51			PB51A			Units
		Min	Typ	Max	Min	Typ	Max	
Offset Voltage, initial			±0.75	±1.75		*	±1.0	V
Offset Voltage vs. Temperature	Full temp range[1]		-4.5	-7		*	*	mV/°C
Input Impedance, DC		25	50		*	*		kΩ
Input Capacitance			3			*		pF
Closed Loop Gain Range		3	10	25	*	*	*	V/V
Gain Accuracy, internal Rg, Rf	A_V = 3		±10	±15		*	*	%
Gain Accuracy, external Rf	A_V = 10		±15	±25		*	*	%
Phase Shift	f=10 kHz, AVC_L = 10, C_C = 22pF		10			*		°
	f =200 kHz, AVC_L = 10, C_C = 22pF		60			*		°

1. Guaranteed by design but not tested.

OUTPUT

Parameter	Test Conditions	PB51			PB51A			Units
		Min	Typ	Max	Min	Typ	Max	
Voltage Swing	I_O = 1.5A (PB51), 2A (PB51A)	$\pm V_S$−11	$\pm V_S$−8		$\pm V_S$−15	$\pm V_S$−11		V
Voltage Swing	I_O = 1A	$\pm V_S$−10	$\pm V_S$−7		*	*		V
Voltage Swing	I_O = 0.1A	$\pm V_S$−8	$\pm V_S$−5		*	*		V
Current, continuous		1.5			2.0			A
Slew Rate	Full temp range	50	100		75	*		V/µs
Capacitive Load	Full temp range		2200			*		pF
Settling Time to 0.1%	R_L = 100, 2V step		2			*		µs
Power Bandwidth	V_C = 100 V_{P-P}	160	230		240	*		kHz
Small Signal Bandwidth	C_C=22pF, A_V=25, V_{CC} = ±100		100			*		kHz
Small Signal Bandwidth	C_C =22pF, A_V=3, V_{CC} = ±30		1			*		MHz

POWER SUPPLY

Parameter	Test Conditions	PB51			PB51A			Units
		Min	Typ	Max	Min	Typ	Max	
Voltage, $\pm V_S$ [1]	Full temp range	±15[2]	±60	±150	*	*	*	V
Current, quiescent	V_S = ±15 V_S = ±60 V_S = ±150		11 12 14	18		* * *	*	mA mA mA

1. +V_S and −V_S denote the positive and negative supply rail respectively.
2. +V_S/−V_S must be at least 15V above/below COM.

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THERMAL

Parameter	Test Conditions	PB51			PB51A			Units
		Min	Typ	Max	Min	Typ	Max	
Resistance, AC, junction to case [1]	Full temp range, f > 60 Hz		1.2	1.3		*	*	°C/W
Resistance, DC, junction to case	Full temp range, f < 60 Hz		1.6	1.8		*	*	°C/W
Resistance, junction to air	Full temperature range		30			*		°C/W
Temperature Range, case	Meets full range specs	-25	+25	+85	*	*	*	°C

1. Rating applies if the output current alternates between both output transistors at a rate faster than 60 Hz.

Note: * The specification of PB51A is identical to the specification for PB51 in applicable column to the left.

TYPICAL PERFORMANCE GRAPHS

Figure 3: Power Derating
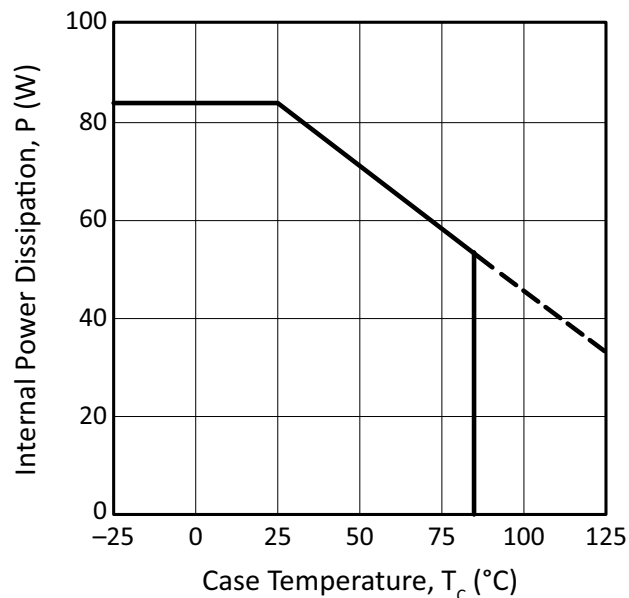
Figure 4: Current Limit
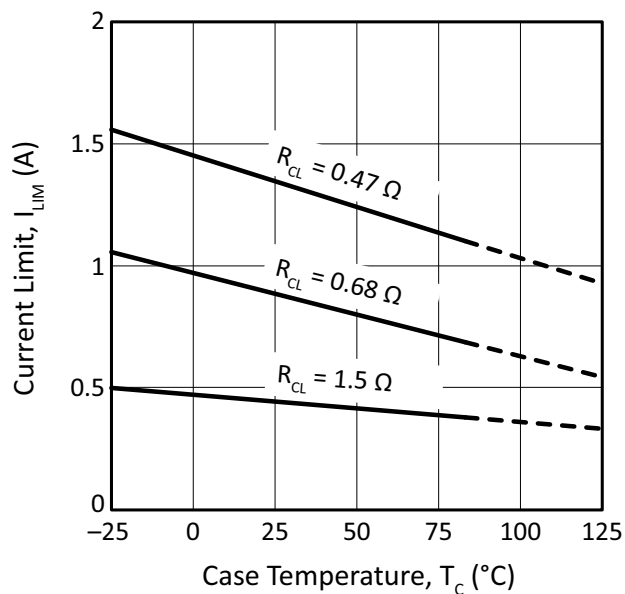
Figure 5: Output Voltage Swing
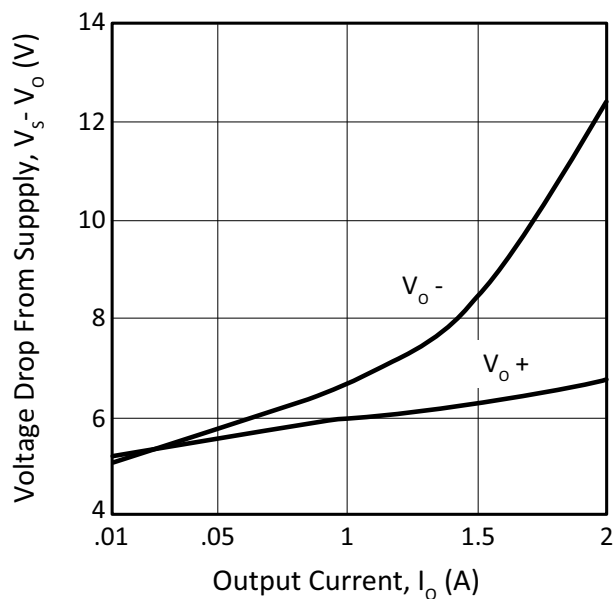
Figure 6: Small Signal Response
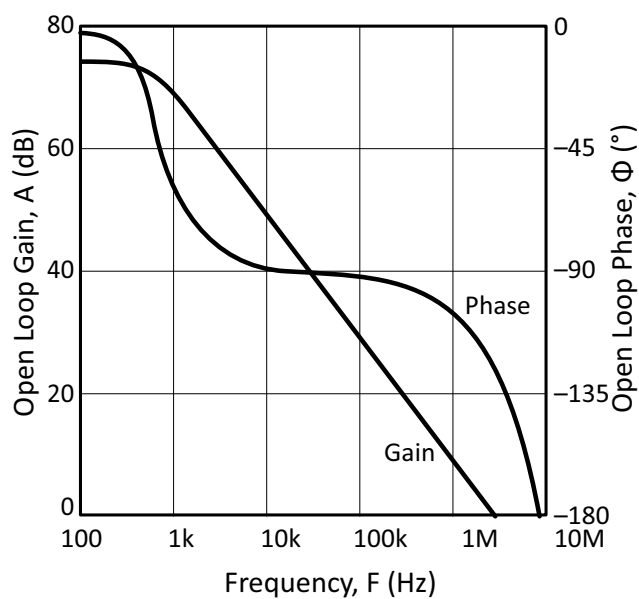
Figure 7: Small Signal Response
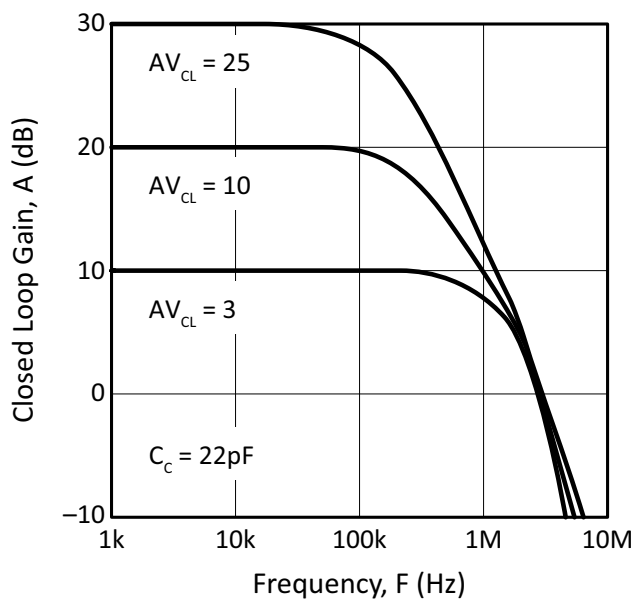
Figure 8: Small Signal Response
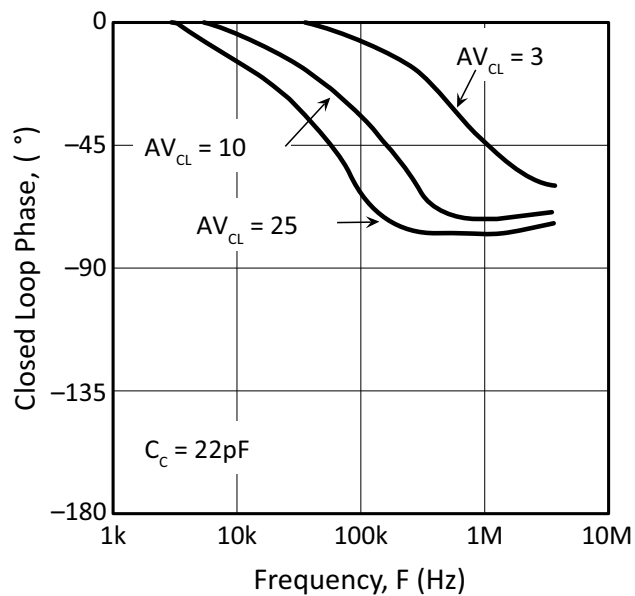
Figure 9: Quiescent Current
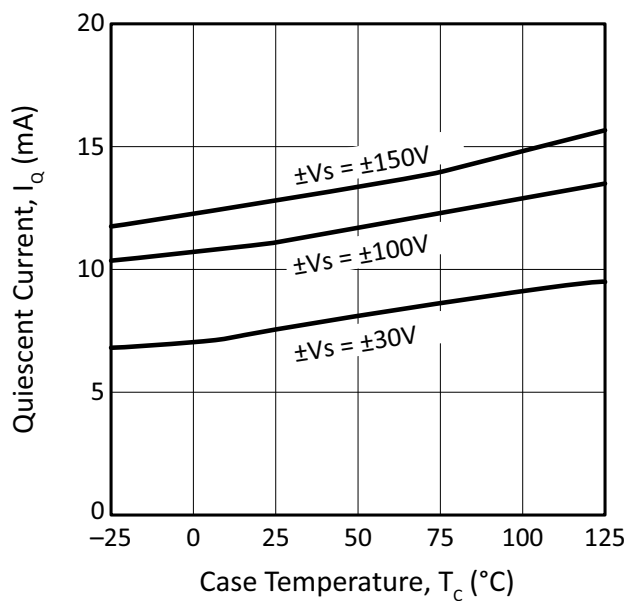
Figure 10: Input Offset Voltage
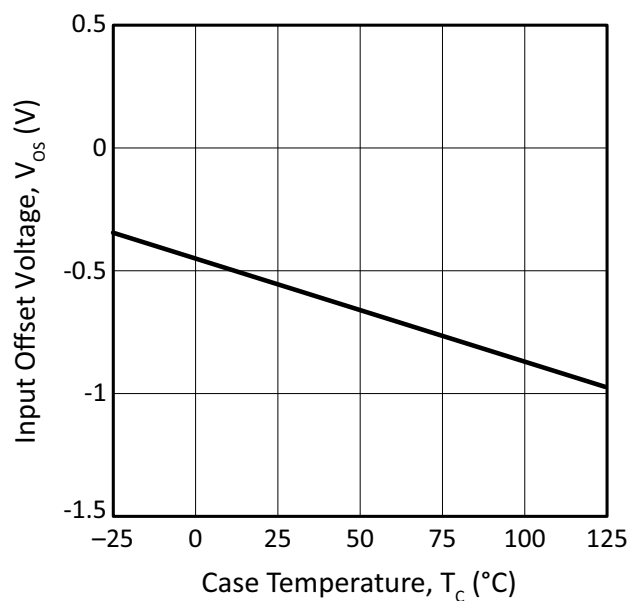
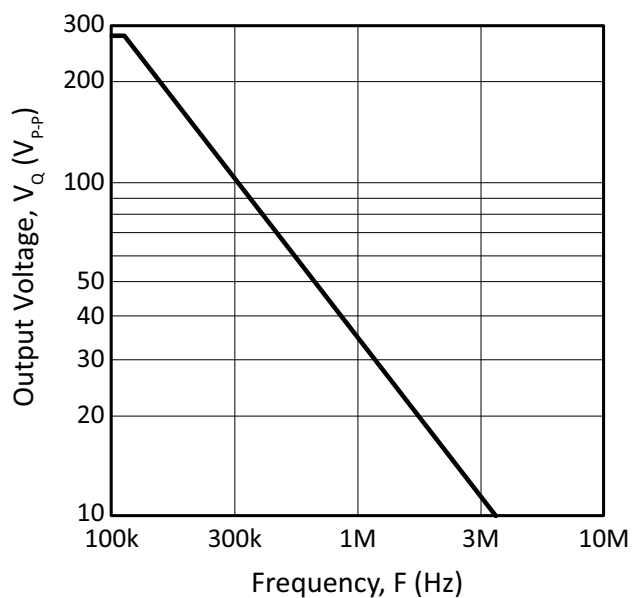### Figure 11: Slew Rate vs. Temperature
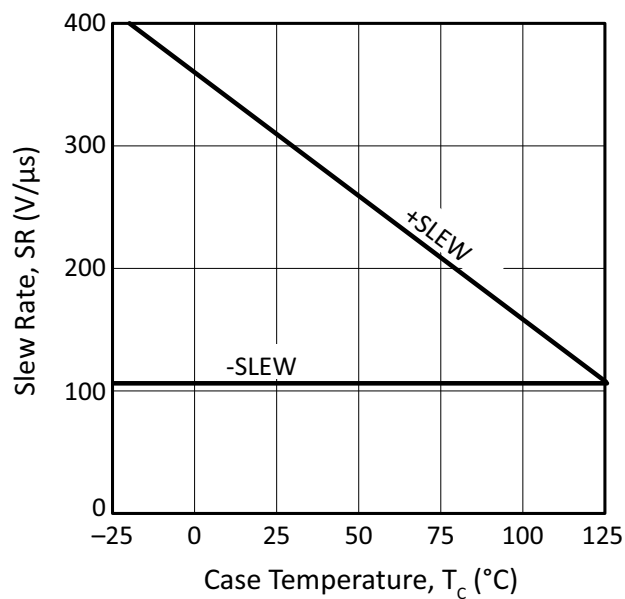
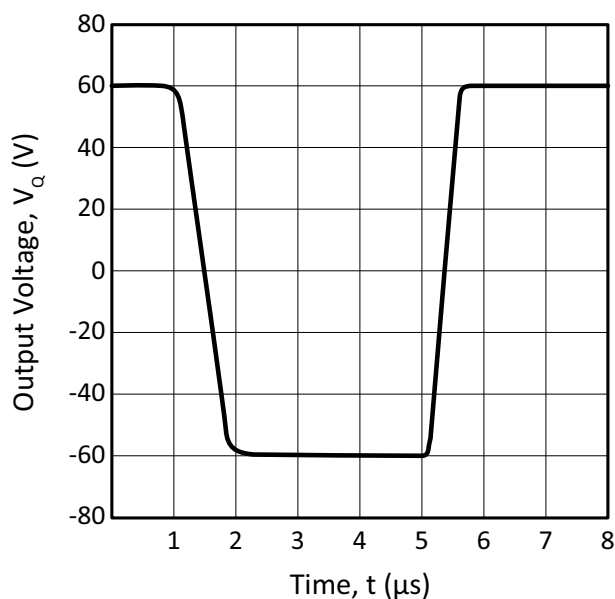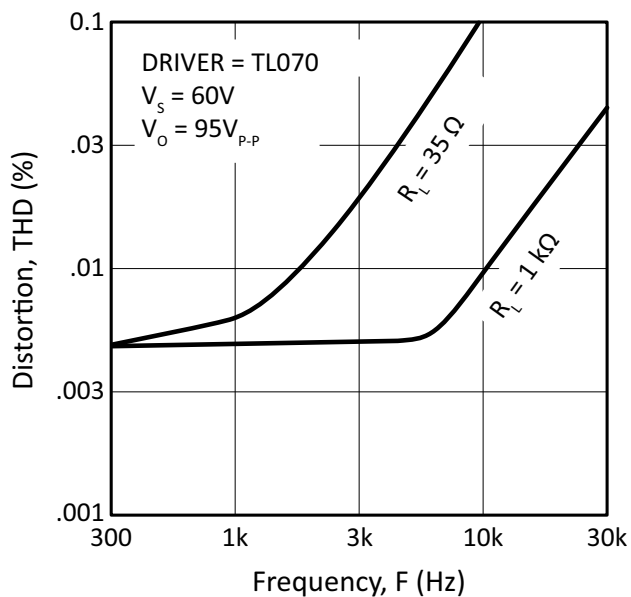### Figure 12: Power Response

Figure 13: Pulse Response

Figure 14: Harmonic Distortion

SAFE OPERATING AREA (SOA)

Note: The output stage is protected against transient flyback. However, for protection against sustained, high energy flyback, external fast-recovery diodes should be used.

Figure 15: SOA
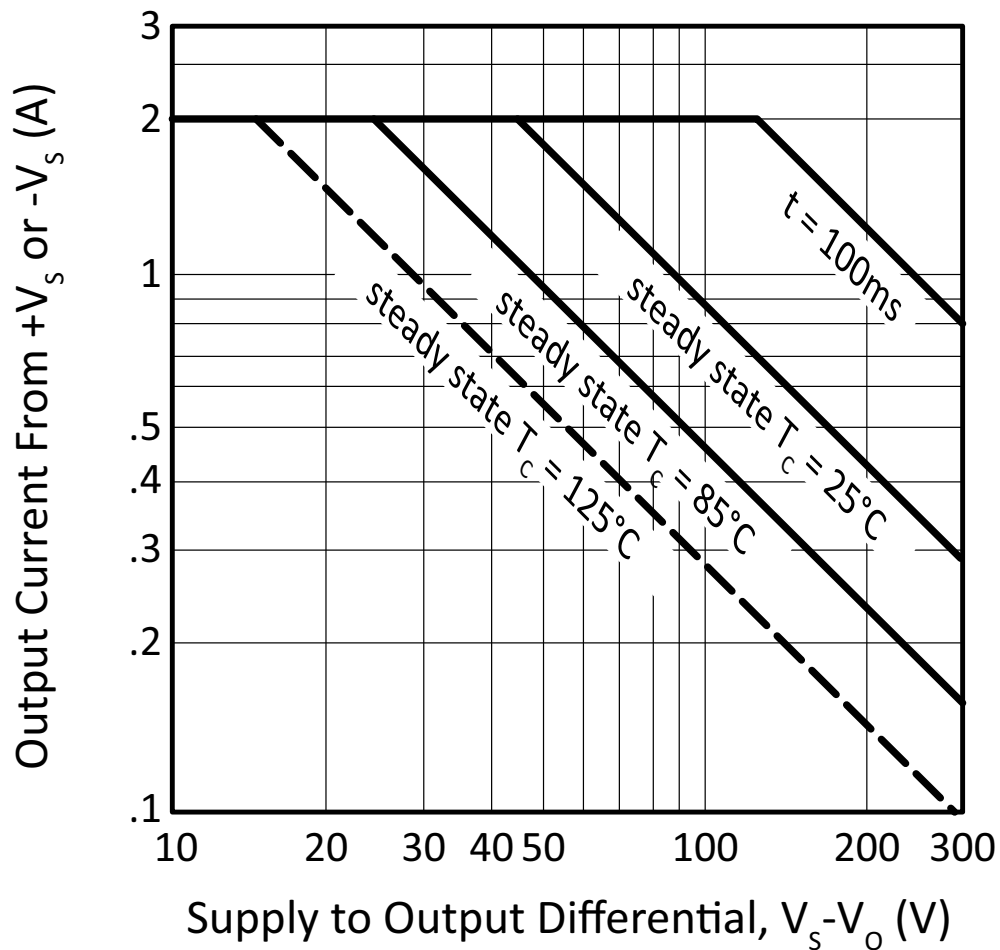
GENERAL

Please read Application Note 1, "General Operating Considerations" which covers stability, supplies, heat sinking, mounting, current limit, SOA interpretation, and specification interpretation. Visit www.apexana-log.com for Apex Microtechnology's complete Application Notes library, Technical Seminar Workbook, and Evaluation Kits.

TYPICAL APPLICATION

Figure 16: Typical Application
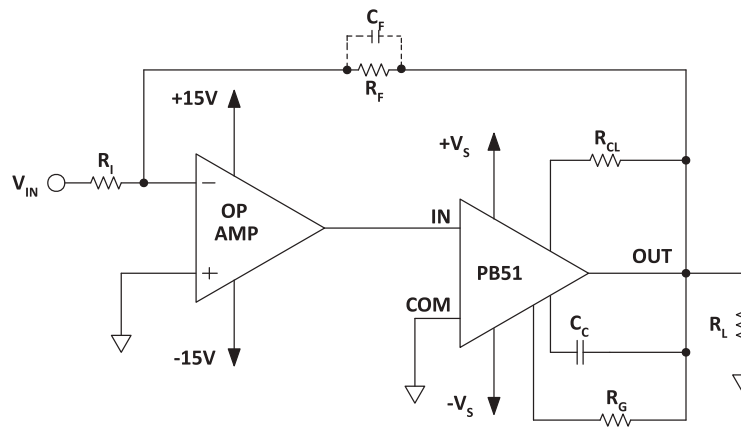
CURRENT LIMIT

For proper operation, the current limit resistor (R_{CL}) must be connected as shown in the external connection diagram. The minimum value is 0.33 with a maximum practical value of 47. For optimum reliability the resistor value should be set as high as possible. The value is calculated as follows:

$$I_{CL} = \frac{0.65\,V}{R_{CL}} + 0.01A \qquad -I_{CL} = \frac{0.65\,V}{R_{CL}}$$

COMPOSITE AMPLIFIER CONSIDERATIONS

Cascading two amplifiers within a feedback loop has many advantages, but also requires careful consideration of several amplifier and system parameters. The most important of these are gain, stability, slew rate, and output swing of the driver. Operating the booster amplifier in higher gains results in a higher slew rate and lower output swing requirement for the driver, but makes stability more difficult to achieve.

GAIN SET

The booster's closed-loop gain is given by the equation below. The composite amplifier's closed loop gain is determined by the feedback network, that is: –Rf/Ri (inverting) or 1+Rf/Ri (non-inverting). The driver amplifier's "effective gain" (Av) is equal to the composite gain divided by the booster gain.

$$R_G = [(Av - 1) \cdot 3.1k] - 6.2k$$

$$Av = \frac{R_G + 6.2k}{3.1k} + 1$$
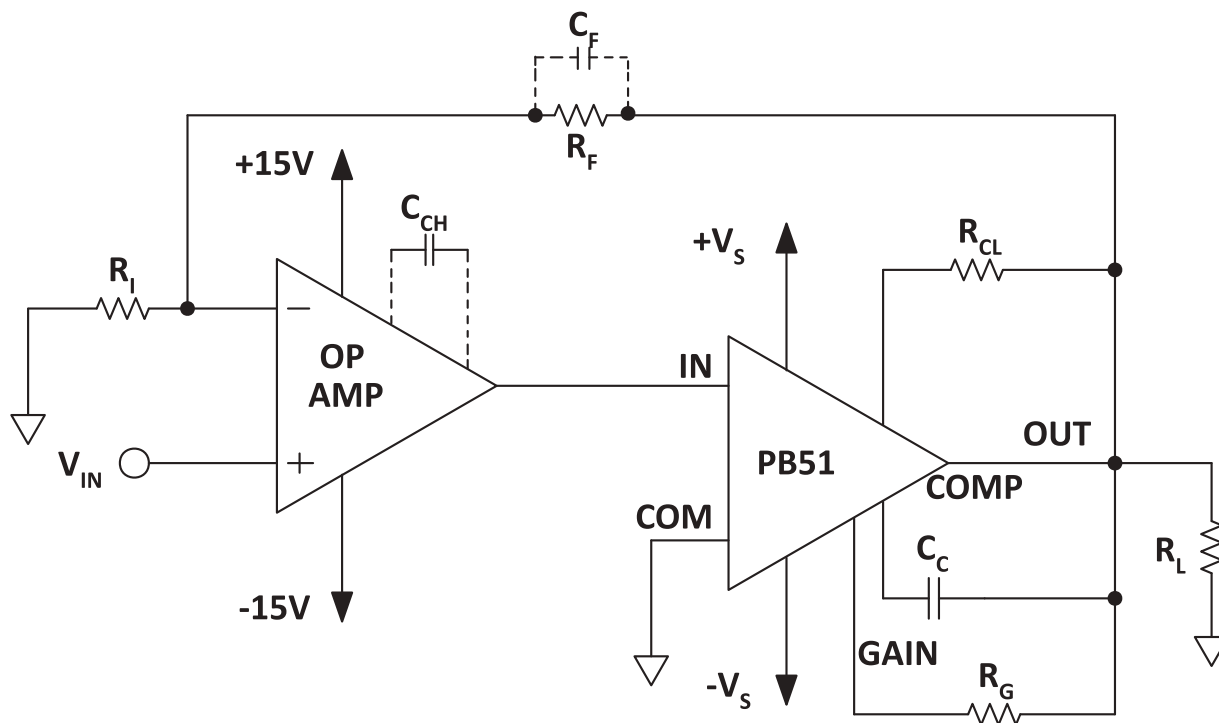
Example: Inverting configuration (figure 17) with
Ri = 2 k, Rf = 60 k, Rg = 0:
Av (booster) = (6.2 k/3.1 k) + 1 = 3
Av (composite) = 60 k/2 k = – 30
Av (driver) = – 30/3 = –10

Figure 17: Composite Amplifier Example

STABILITY

Stability can be maximized by observing the following guidelines:
1. Operate the booster in the lowest practical gain.
2. Operate the driver amplifier in the highest practical effective gain.
3. Keep gain-bandwidth product of the driver lower than the closed loop bandwidth of the booster.
4. Minimize phase shift within the loop.

A good compromise for (1) and (2) is to set booster gain from 3 to 10 with total (composite) gain at least a factor of 3 times booster gain. Guideline (3) implies compensating the driver as required in low composite gain configurations. Phase shift within the loop (4) is minimized through use of booster and loop compensation capacitors Cc and Cf when required. Typical values are 5pF to 33pF.

Stability is the most difficult to achieve in a configuration where driver effective gain is unity (ie; total gain = booster gain). For this situation, Table 1 gives compensation values for optimum square wave response with the op amp drivers listed.

Table 1: Example Drivers

DRIVER	C_{CH}	C_F	C_C	FPBW	SR
OP07	-	22p	22p	4kHz	1.5
741	-	18p	10p	20kHz	7
LF155	-	4.7p	10p	60kHz	>60
LF156	-	4.7p	10p	80kHz	>60
TL070	22p	15p	10p	80kHz	>60
For: R_F = 33K, R_I = 3.3K, R_G = 22K					

TYPICAL VALUES FOR CASE WHERE OP AMP
EFFECTIVE GAIN = 1.

SLEW RATE

The slew rate of the composite amplifier is equal to the slew rate of the driver times the booster gain, with a maximum value equal to the booster slew rate.

OUTPUT SWING

The maximum output voltage swing required from the driver op amp is equal to the maximum output swing from the booster divided by the booster gain. The Vos of the booster must also be supplied by the driver, and should be subtracted from the available swing range of the driver. Note also that effects of Vos drift and booster gain accuracy should be considered when calculating maximum available driver swing.

PACKAGE OPTIONS

| Part Number	Apex Package Style	Description
PB51	DP	12-pin SIP
PB51A	DP	12-pin SIP
PB51EE	EE	12-pin SIP w/ formed leads
PB51EEA	EE	12-pin SIP w/ formed leads

PACKAGE STYLE DP
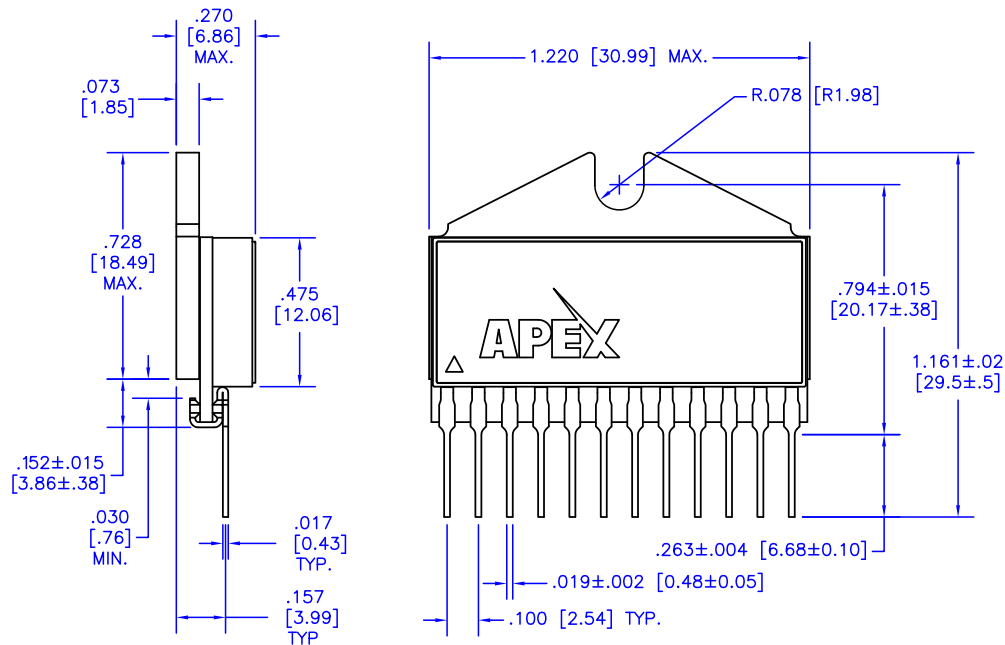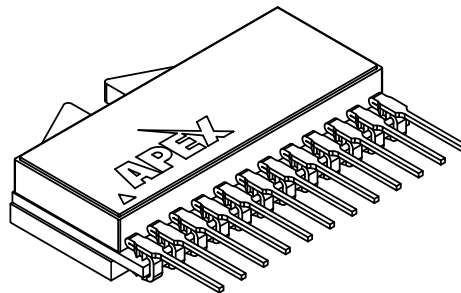
NOTES:
1. Dimensions are inches & [mm].
2. Triangle on lid denotes pin 1.
3. Pins: Alloy 510 phosphor bronze plated with matte tin (150 − 300μ") over nickel (50 μ" max.) underplate.
4. Package: Vectra liquid crystal polymer, black
5. Epoxy−sealed & ultrasonically welded non−hermetic package.
6. Package weight: .367 oz. [11.41 g]

PACKAGE STYLE EE

90°

.088
[2.24]

.09
[2.2]

.120
[3.05]
MIN.

.86
[21.84]
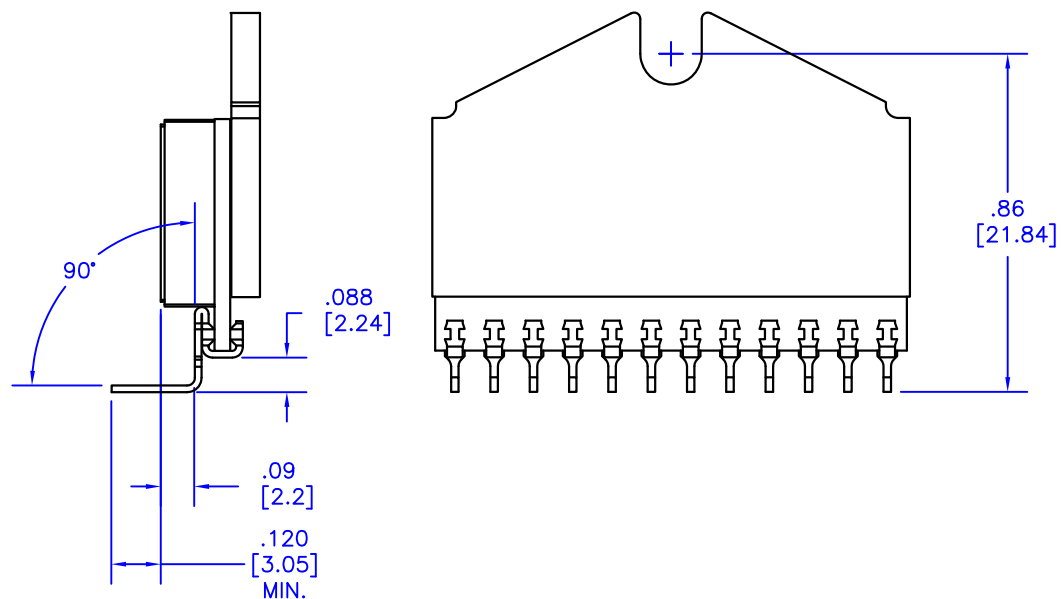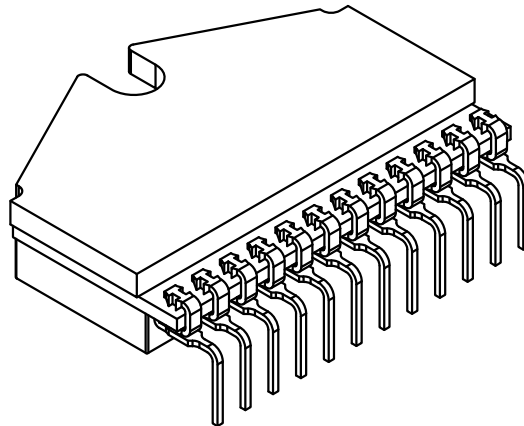
NOTES:
1. Dimensions are inches & [mm].
2. For other dimensions and information on this package with unformed leads, see package DP.

NEED TECHNICAL HELP? CONTACT APEX SUPPORT!

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